

FORM PTO-892 (REV. 3-78)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		SERIAL NO. 697830	GROUP/ART UNIT 258	ATTACHMENT TO PAPER NUMBER 2	
NOTICE OF REFERENCES CITED				APPLICANT(S) Huang et al			
U.S. PATENT DOCUMENTS							
*	DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
A	4 9 1 6 4 9 8	4/10/90	Berenz	357	22A	7	
B	4 8 2 1 0 9 3	4/11/89	Iafrate et al	357	22A		
C	4 6 0 0 9 3 2	7/15/86	Norris	357	22A		
D	4 6 5 2 8 9 6	3/24/87	Das et al	357	22A		
E	5 0 0 8 7 1 7	4/16/91	Bar-Joseph et al	357	22A		
F							
G							
H							
I							
J							
K							
FOREIGN PATENT DOCUMENTS							
*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG. SPEC.
-L	1-19 9 4 7 5	8/89	Japan	Matsumoto	357	22A	7
-M	6 3-3 1 8 1 6 5	12/88	Japan	Yamane	357	22A	
-N	5 9-1 1 9 7 6 8	7/84	Japan	Ishikawa	357	22MD	
-O	5 9-4 0 8 5	1/84	Japan	Muton	357	22MD	
-P	1-9 4 6 7 4	4/89	Japan	Nagami	357	22A	
-Q	1-1 2 8 4 7 3	5/89	Japan	Isaue	357	22A	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
R	IEEE Electron Device Letters, Vol. 10, No. 10, October 1989, "A 0.25-um Gate-Length Pseudomorphic HFET with 32-mW Output Power at 94 GHz" by Smith et al, P. 437-P. 439.						
T	IEEE Electron Device Letters, Vol. 11, No. 1, January 1990, "W-Band Low-Noise InAlAs/InGaAs Lattice-Matched HEMT's" by Chao et al, P. 59-P. 62.						
EXAMINER		DATE					
Loke		10/16/91					
* A copy of this reference is not being furnished with this office action. (See Manual of Patent Examining Procedure, section 707.05 (a).)							